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## A94

## PNP EPITAXIAL SILICON TRANSISTOR

### HIGH VOLTAGE TRNSISTOR

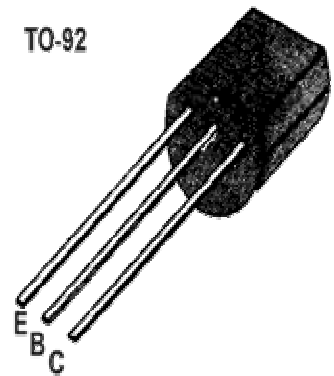
\*High Collector-Emitter Voltage:  $V_{CEO} = -400V$

\*Low Collector-Emitter Saturation Voltage

\*Complement to A44

### ABSOLUTE MAXIMUM RATINGS(TA=25 )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-400	V
Collector-Emitter Voltage	$V_{CEO}$	-400	V
Emitter -Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-300	mA
Collector Dissipation	$P_C$	625	mW
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	



### ELECTRCAL CHARACTERISTICS(TA=25 )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -100 \mu A, I_E = 0$	-400			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -100 \mu A, I_C = 0$	-6			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -300V, I_E = 0$			-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{BE} = -4V, I_C = 0$			-100	nA
*DC Current Gain	HFE1	$V_{CE} = -10V, I_C = -1mA$	40			
	HFE2	$V_{CE} = -10V, I_C = -10mA$	50		300	
	HFE3	$V_{CE} = -10V, I_C = -50mA$	45			
	HFE4	$V_{CE} = -10V, I_C = -100mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-500	mV
	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-750	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$			-750	mV
Collector-Base Capacitance	$C_{CB}$	$V_{CB} = -20V, I_E = 0, F = 1MHz$		7		pF